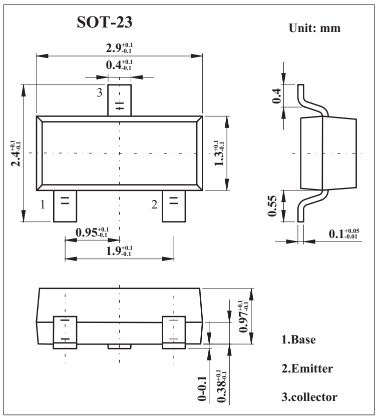
Silicon RF Switching Diode

BAT18;BAT18-04
BAT18-05;BAT18-06



■ Features

- ● Low-loss VHF/UHF switch above 10 MHz
- ● Pin diode with low forward resistance

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	35	V
Forward Current	I_F	100	mA
Operating and storage temperature range	T_{op}, T_{stg}	-55 to +150	℃
Junction - ambient	$R_{th\ JA}$	≤450	K/W

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V_F	I_F = 100 mA		0.38	1.2	V
Reverse current	I_R	V_R = 20 V			20	nA
		V_R = 20 V, T_A = 60℃			200	
Diode capacitance	C_T	V_R = 20 V, f = 1 MHz		0.75	1	pF
Forward resistance	rf	I_F = 5 mA, f = 100 MHz		0.4	0.7	Ω
Series inductance	L_s			2		nH

■ Marking

Type	BAT18	BAT18-04	BAT18-05	BAT18-06
Marking	A2	AU	AS	AT